ECR Plasma Enhanced Sputtering and Applications

Seong Bong Kim¹, Seungil Park¹, Changho Yi¹, Wan-woo Park², Jeong-rak Lee², Jae-chul Do², Woo-jin Choi²,

and Sung Haeng Cho³

¹National Fusion Research Institute, Korea, Republic of

²AVACO Co., LTD., Korea, Republic of

³Electronics and Telecommunications Research Institute, Korea, Republic of

We have developed an ECR plasma enhanced sputtering (ECRES) system which isconsisted of a rotary target with length of 1500 mm and two microwavelaunchers. In the previous work, ECR plasma sources were investigated and theirmagnetic field configuration were similar to conventional magnetron sputteringcathodes such as circular or linear types [1]. The results showed that thelab-scale ECR plasma sources could have stable plasmas with high density nearthe metal targets under low operating pressure less than 1 mTorr without anypower at the metal targets. It means that the ECR plasma sources can decouple power for plasma generation and the bias voltage for acceleration of ionsonto the target surface. In the present work, the ECRES system has beendeveloped, which has high magnetic field than the magnetic field ofconventional rotary cathodes. The characteristics of plasmas and thin filmshave been studied. In this talk, first the concept and design of the ECRESsystem would be introduced, secondly, the characteristics of plasmas and thinfilms would be showed and finally, the application of oxide TFT would bediscussed.

REFERENCES:

[1] Kim etal. "Design and characterization of 2.45 GHz electron cyclotron resonance plasmasource with magnetron magnetic field configuration for high flux ofhyperthermal neutral beam", Rev. Sci. Instrum. Vol. 81, pp 083301, 2010.

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